

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-57 (Canceled).

58. (Currently Amended) A gallium nitride based compound semiconductor light-emitting device comprising:

a semiconductor stacked structure including an n-type gallium nitride based compound semiconductor layer and a p-type gallium nitride based compound semiconductor layer;

a light-transmitting, first electrode, through which light can pass, provided over a surface of the p-type gallium nitride based compound semiconductor layer;

a second electrode for bonding, provided on a surface of the p-type gallium nitride based compound semiconductor layer and on a portion of the first electrode, the second electrode being , and electrically connected to the first electrode,

said second electrode contacting with the p-type gallium nitride based compound semiconductor layer and being adhered to the p-type gallium nitride based compound semiconductor layer stronger than a bond of the p-type gallium nitride based compound semiconductor layer with the first electrode or than a bond of the first electrode with the second electrode.

59. (Previously Presented) The device according to claim 58, wherein the second electrode contacts with the p-type gallium nitride based compound

semiconductor layer through a cut-off portion which is provided in the first electrode, and extends over a portion of the first electrode.

60. (Previously Presented) The device according to claim 58, wherein the first electrode has a thickness of 0.001 to 1 μm .

61. (Previously Presented) The device according to claim 58, wherein the first electrode has a thickness of 0.005 to 02 μm .

62. (Previously Presented) The device according to claim 58, wherein the second electrode constitutes a bonding pad.